

### **Description**

APL0501A device is low R<sub>ON</sub> MOSEFT controlled by external logic pin, allowing optimization of battery life, and portable device autonomy. It includes a P-channel MOSFET that operates over an input voltage range of 1.2V to 5.5V. An on/off input (ON) controls the switch that can interface with low voltage control signals. A  $130\Omega$  on chip load resistor is added for output quick discharge when the switch is turned off. APL0501A is packaged in WLCSP-4 with 0.4mm pitch. It is characterized for operation over the free-air temperature range of -40°C to 85°C.

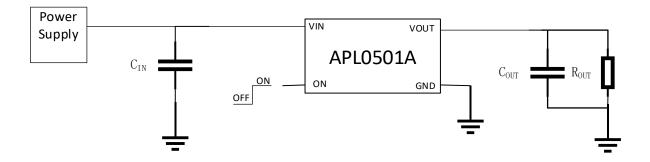
### **Applications**

- Cellular Phones
- GPS Devices
- Digital Cameras
- Peripheral Ports
- Portable Instrumentation
- RF Modules
- Personal Digital Assistants (PDAs)
- MP3 Players

#### **Features**

- Low-Input Voltage: 1.2V to 5.5V
- Ultra-Low ON-State Resistance
  - $R_{ON}$ =48m $\Omega$  at VIN=5.0V
  - $R_{ON}$ =53m $\Omega$  at VIN=4.2V
  - $R_{ON}$ =56m $\Omega$  at VIN=3.6V
  - $\bullet$  R<sub>ON</sub>=67m $\Omega$  at VIN=2.5V
  - $\bullet$  R<sub>ON</sub>=87m $\Omega$  at VIN=1.8V
  - R<sub>ON</sub>=160mΩ at VIN=1.2V
- DC Current Up to 1.5A
- Ultra-Low Quiescent Current: 80nA at 1.8V
- Ultra-Low Shutdown Current: 7.5nA at 1.8V
- Low Control Input Thresholds Enable Use of 1.2V/1.8V/3.6V/4.2V/5.0V Logic
- Controlled Slew Rate to Avoid Inrush Current
- Reverse Current Protection
- Package: WLCSP-4 (0.4mm Pitch)

### **Typical Application**



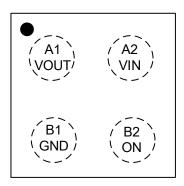


## **Package and Order Information**

Part Number	Package	Temperature	Packaging	Marking
	Description	Range	Option	Information
APL0501A	WLCSP-4	-40°C ~ 85°C	3000/Tape & Reel	AXX

### **Pin Configuration and Top Mark**

(Top View)



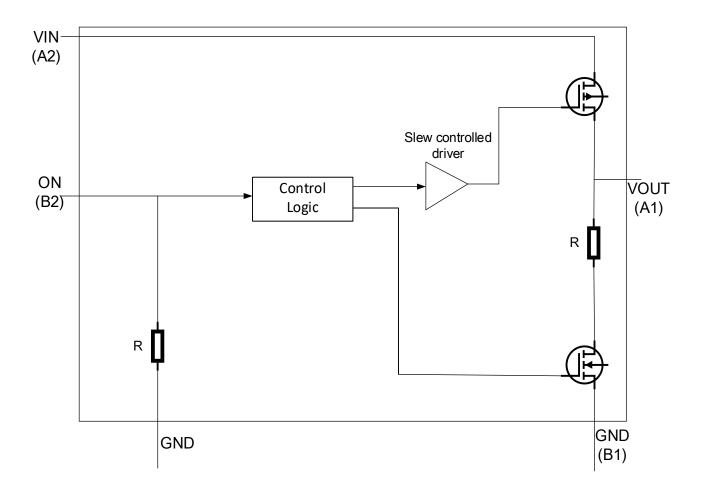
WLCSP-0.8x0.8-4B

### **Pin Assignments**

Name	NO.	Description	
VOUT	A1	Switch output	
VIN	A2	Switch input, a bypass capacitor should be connected to ground together with it	
GND	B1	Ground	
ON	B2	Switch control input, active high	



### **Functional Block Diagram**





## Absolute Maximum Ratings (T<sub>A</sub> = 25°C unless otherwise specified)

Symbol	Parameter	Rating	Unit
V <sub>IN</sub>	Input voltage	-0.3 to 6	V
V <sub>OUT</sub>	Output voltage	V <sub>IN</sub> + 0.3	V
V <sub>ON</sub>	Input voltage	-0.3 to 6	V
$P_D$	Power dissipation at T <sub>A</sub> =25°C	0.48	W
I <sub>MAX</sub>	Maximum continuous switch current	2	А
T <sub>A</sub>	Operating free air temperature range	-40 to 85	°C
T <sub>LEAD</sub>	Maximum lead temperature (10s soldering time)	300	°C
T <sub>STG</sub>	Storage temperature	-45 to 145	°C
$\theta_{JA}$	Thermal Resistance	190	°C/W
ESD	HBM: All Pins	±4000	V
LOD	CDM	±1000	V
Latch up		±200	mA

## **Recommend Operating Conditions**

Symbol	Parameter	Rating	Unit
Vin	Input voltage range	1.2 to 5.5	V
Vouт	Output voltage range	Vin	V
Cin	Input capacitor	1	μF



# Electrical Characteristics (T<sub>A</sub> = 25°C unless otherwise specified)

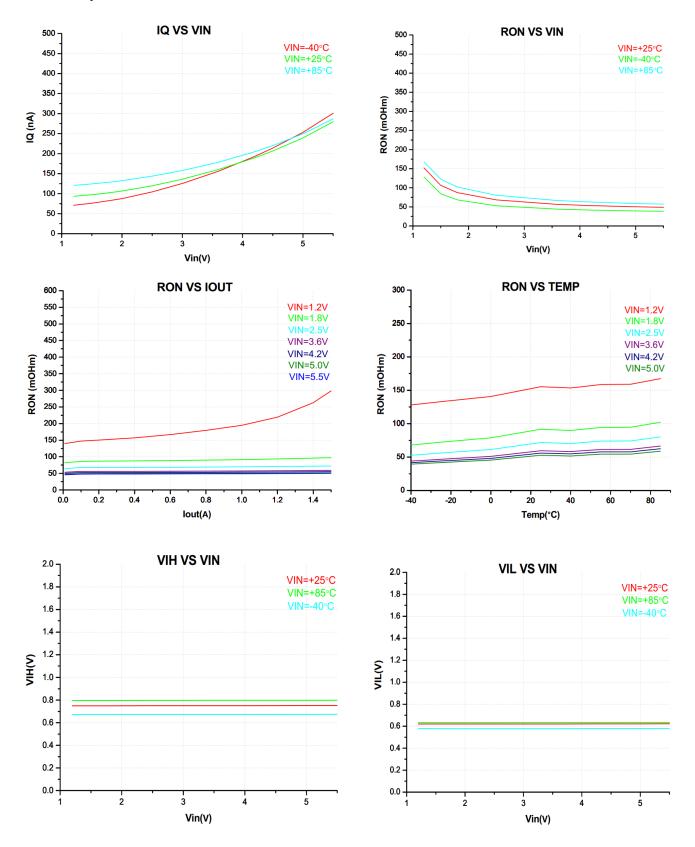
Symbol	Parameter	Condition	Conditions		Тур.	Max.	Unit
			V <sub>IN</sub> =1.2V	40	75	130	
			V <sub>IN</sub> =1.8V		80		nA
lα	Quiescent current	Iout=0, Vin=Von	V <sub>IN</sub> =3.6V	90	119	250	
			V <sub>IN</sub> =4.2V		142		
			V <sub>IN</sub> =5.0V	150	188	350	
			V <sub>IN</sub> =1.2V		7	20	
			V <sub>IN</sub> =1.8V		7.5		
Isp	OFF-state supply current	V <sub>ON</sub> =GND, V <sub>OUT</sub> =Open	V <sub>IN</sub> =3.6V		10	30	nA
		V <sub>001</sub> -Open	V <sub>IN</sub> =4.2V		12		
			V <sub>IN</sub> =5.0V		20	50	
	OFF-state supply current	Von=GND, Vout=0	V <sub>IN</sub> =1.2V		7.5		nA
			V <sub>IN</sub> =1.8V		8		
Ilkg			V <sub>IN</sub> =3.6V		10		
			V <sub>IN</sub> =4.2V		12.5		
			VIN=5.0V		20.5		
	ON-state resistance	louт=-200mA	V <sub>IN</sub> =1.2V	140	160	190	- mΩ
			V <sub>IN</sub> =1.8V		87		
Б			V <sub>IN</sub> =2.5V		68		
Ron			VIN=3.6V		56		
			V <sub>IN</sub> =4.2V		53		
			VIN=5.0V	30	48	70	
lrev	Reverse current during disable	V <sub>OUT</sub> =5.0V, V <sub>ON</sub> =0, V <sub>IN</sub> =0V			14		nA
Ron_pd	ON pull down resistance				100		ΜΩ
Rpd	Output pull down resistance	Vin=3.3V, Von=0			130	150	Ω
ViH	High level input voltage	V <sub>IN</sub> =1.2V to 5.5V		1.0			V
VIL	Low level input voltage	V <sub>IN</sub> =1.2V to	V <sub>IN</sub> =1.2V to 5.5V			0.5	V



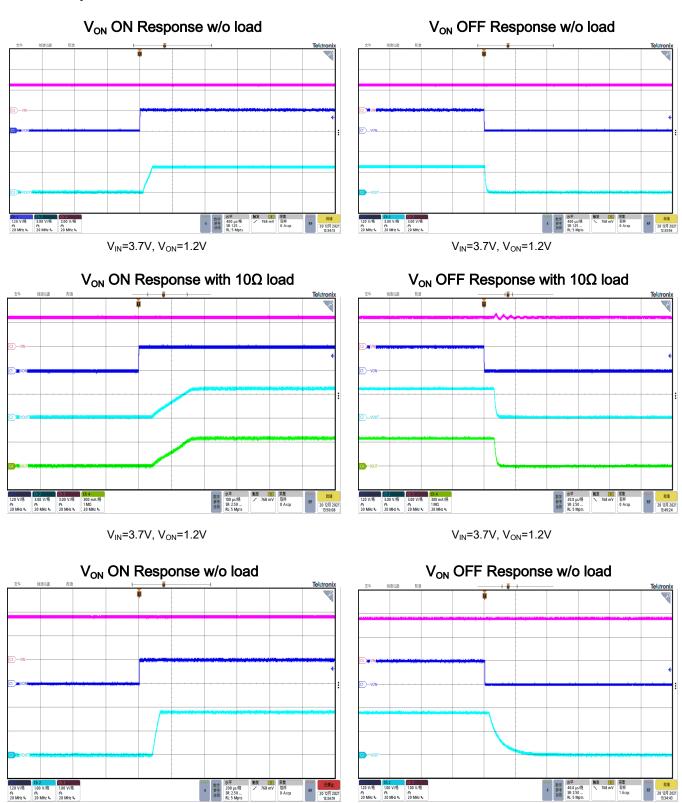
# Switching Characteristics ( $T_A = 25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Conditions		Min.	Тур.	Max.	Unit
V <sub>IN</sub> =1.2V							
t <sub>ON</sub>	Turn on time	R <sub>L</sub> =500Ω	C <sub>L</sub> =0.1µF		370		μs
t <sub>OFF</sub>	Turn off time	R <sub>L</sub> =500Ω	C <sub>L</sub> =0.1µF		10		us
t <sub>R</sub>	VOUT rise time	R <sub>L</sub> =500Ω	C <sub>L</sub> =0.1µF		29		μs
t <sub>F</sub>	VOUT fall time	R <sub>L</sub> =500Ω	C <sub>L</sub> =0.1µF		26		μs
V <sub>IN</sub> =1.8V							
t <sub>ON</sub>	Turn on time	R <sub>L</sub> =500Ω	C <sub>L</sub> =0.1µF		145		μs
t <sub>OFF</sub>	Turn off time	R <sub>L</sub> =500Ω	C <sub>L</sub> =0.1µF		13		us
t <sub>R</sub>	VOUT rise time	R <sub>L</sub> =500Ω	C <sub>L</sub> =0.1µF		46		μs
t <sub>F</sub>	VOUT fall time	R <sub>L</sub> =500Ω	C <sub>L</sub> =0.1µF		27		μs
V <sub>IN</sub> =3.6V							
t <sub>ON</sub>	Turn on time	R <sub>L</sub> =500Ω	C <sub>L</sub> =0.1µF		117		μs
t <sub>OFF</sub>	Turn off time	R <sub>L</sub> =500Ω	C <sub>L</sub> =0.1µF		14		us
t <sub>R</sub>	VOUT rise time	R <sub>L</sub> =500Ω	C <sub>L</sub> =0.1µF		110		μs
t <sub>F</sub>	VOUT fall time	R <sub>L</sub> =500Ω	C <sub>L</sub> =0.1µF		26		μs
V <sub>IN</sub> =4.2V							
t <sub>ON</sub>	Turn on time	R <sub>L</sub> =500Ω	C <sub>L</sub> =0.1µF		119		μs
t <sub>OFF</sub>	Turn off time	R <sub>L</sub> =500Ω	C <sub>L</sub> =0.1µF		14		us
t <sub>R</sub>	VOUT rise time	R <sub>L</sub> =500Ω	C <sub>L</sub> =0.1µF		130		μs
t <sub>F</sub>	VOUT fall time	R <sub>L</sub> =500Ω	C <sub>L</sub> =0.1µF		26		μs
V <sub>IN</sub> =5V				•	•	•	-
t <sub>ON</sub>	Turn on time	R <sub>L</sub> =500Ω	C <sub>L</sub> =0.1µF		119		μs
t <sub>OFF</sub>	Turn off time	R <sub>L</sub> =500Ω	C <sub>L</sub> =0.1µF		14		us
t <sub>R</sub>	VOUT rise time	R <sub>L</sub> =500Ω	C <sub>L</sub> =0.1µF		140		μs
t <sub>F</sub>	VOUT fall time	R <sub>L</sub> =500Ω	C <sub>L</sub> =0.1µF		25		μs





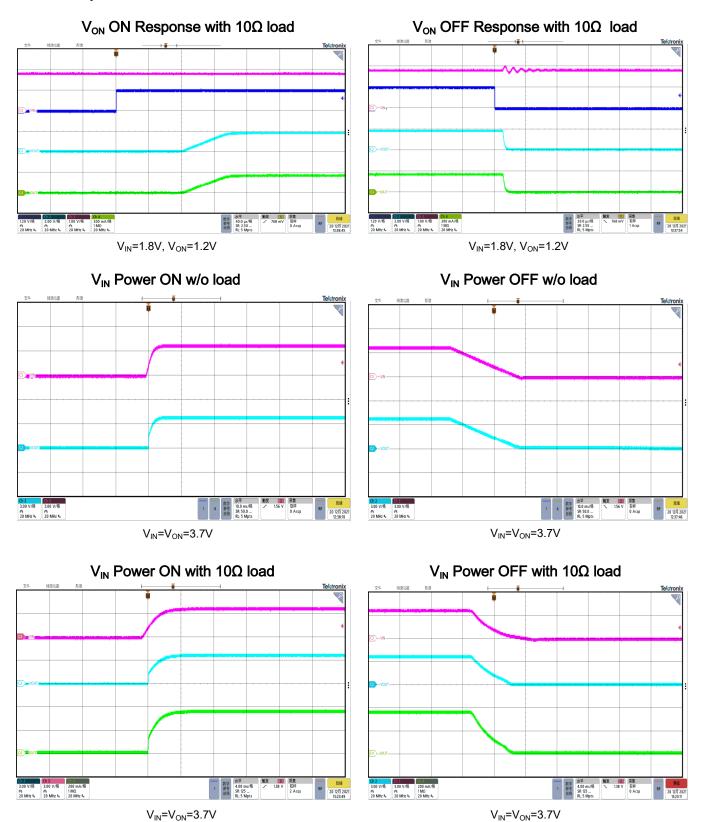




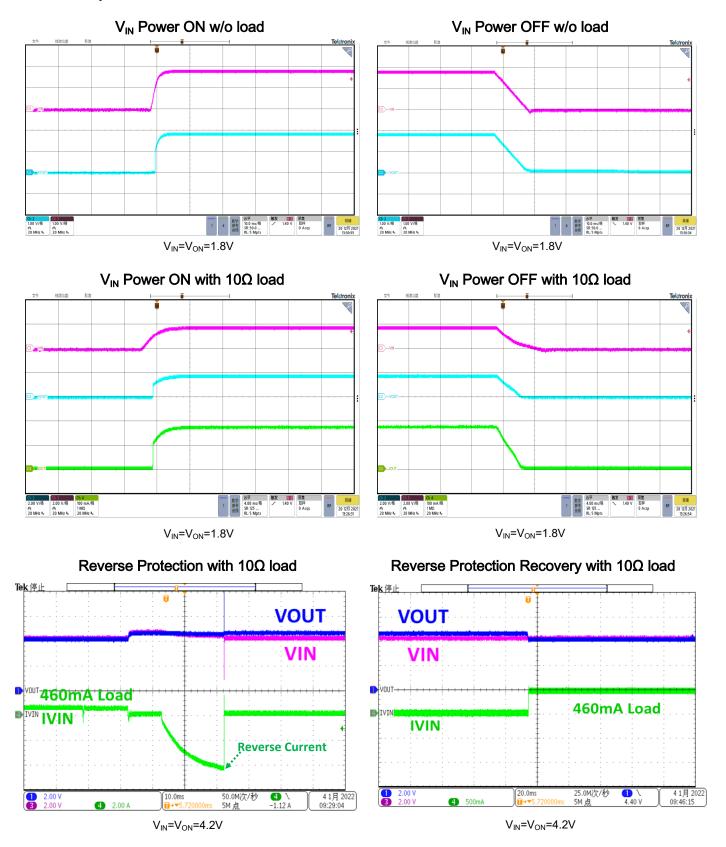
 $V_{IN}$ =1.8V,  $V_{ON}$ =1.2V

 $V_{IN}$ =1.8V,  $V_{ON}$ =1.2V











### **Functional Description**

### **Device Operation**

The APL0501A is a low on-resistance ( $R_{ON}$ ) load switch with controlled turn on, up to 1.5A output current. It contains a P-channel MOSFET and can be turned on with a wide range application of battery from 1.2V to 5.5V. An on/off input (ON) controls the switch, which can interface with low-threshold 1.2V GPIO control signal. A 130 $\Omega$  on-chip output resistor is added for output quick discharge when the switch is switched off.

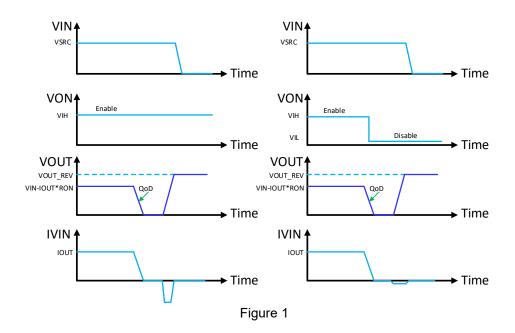
#### **ON/OFF Control**

The pin of ON controls the state of the switch. ON is active HI pin and has a low threshold making it capable of interfacing with low voltage GPIO control signals. It can be used with any microcontroller with 1.2V, 1.8V, 2.5V, 3.3V GPIOs. Applying VIH on the ON pin will put the switch in the on-state and VIL will put the switch in the off-state.

ON (Control Input)	VIN to VOUT	Quick Output Discharge Resistance	
L	OFF	Yes	
Н	ON	No	

#### **Reverse Current Protection**

The device includes a reverse current protection circuit, which stops a reverse current flowing from the VOUT pin to the VIN or GND pin when the voltage on VOUT becomes higher than VIN. This feature is particularly useful when the output of device needs to be driven by another voltage source, whichever device is both disabled and enabled (for example in a power multiplexer application). In order for this feature to work, device has to be disabled, and either of the following conditions shall be met: VIN > 1.2V or VOUT > 1.2V. Meanwhile considering of heat dissipation, VIN input voltage should be limited less than 4.8V voltage when VON is active high.



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### **Functional Description (Continued)**

### **Quick Output Discharge**

The APL0501A integrates the quick output discharge (QOD) feature. When the switch is disabled, a discharge resistance with a typical value of  $130\Omega$  is connected between the output and ground. This resistance pulls down the output and quickly discharges output capacitor charge, and prevents it from floating when the device is disabled.

### **Input Bypass Capacitor**

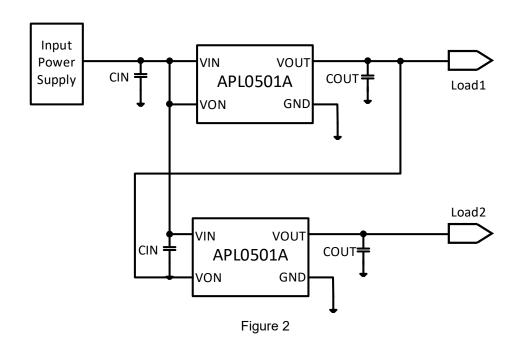
A low ESR ceramic capacitor, X5R or X7R, needs to be placed between VIN and GND to limit the voltage drop on the input supply caused by transient in-rush currents. A typical  $1\mu F$  ceramic capacitor,  $C_{IN}$ , placed close to the pins is usually needed.  $C_{IN}$ 's higher values can be used to further reduce the voltage drop during high current output application. It is recommended that the input capacitor is approximately 10 times higher than the output capacitor to prevent excessive voltage drop when switching heavy loads.

### **Output Bypass Capacitor**

A low ESR ceramic capacitor, X5R or X7R, should be placed between VOUT and GND. A  $0.1\mu F$  ceramic capacitor that is placed close to the IC pins is usually sufficient. This capacitor will prevent parasitic board inductances from forcing VOUT below GND when the switch turns off. It is recommended that  $C_{IN}$  is 10times higher than  $C_{OUT}$  so that once the switch is turned on, COUT can be charged up to VIN without VIN dropping significantly.

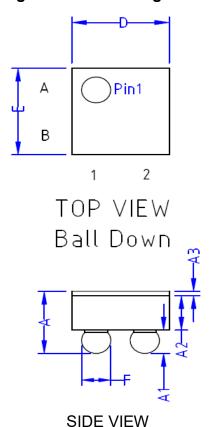
### **Power Supply Sequencing without a GPIO Input Control Port**

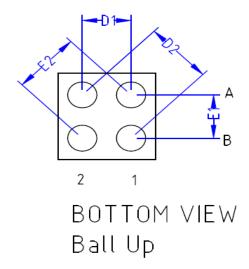
In many terminal devices, each module needs to be powered up in a pre-determined manner. The device can solve the power sequencing problem without increasing any complexity to the overall system. Figure 2 shows the configuration required to power up the two modules in a fixed sequence. The output of the first load switch is tied to the enable of the second load switch, so when load1 is powered, the second load switch is enabled and load2 is powered.





### **Package Outline Drawing**





				Unit:mm
		NO.	Mean	Tolerance
Top Thickness		A	0. 449	±0.036
Ball Height+UBM T	hickness	A1	0. 194	±0.023
Wafer/Grinding Th	A2	0. 215	±0.0125	
Backside Coating Thickness		A3	0. 04	±0.005
Pkg Die Size	X	D	0.775	±0.025
	Y	E	0.775	±0.025
Ball Size afer re	flow	F	0. 268	±0.020
		D1	0.4	NA
D 11 D: ( )	D2	0. 565	NA	
Ball Pitch		E1	0.4	NA
		E2	0. 565	NA

## **Contact Information**

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